

IBS primary business focus is to supply full outsourcing of the ion implantation process to semiconductors manufacturers, labs and universities.

The Total Ion Implantation Solution

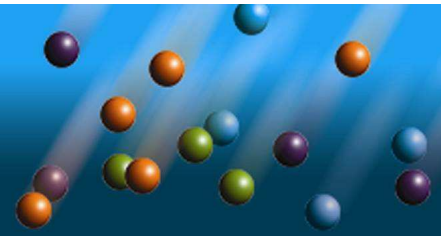
We offer the most complete implant “service” in the industry that can process of wafers and substrates from 2” to 200mm, with 300mm plasma ion implantation also available.

- IBS manufacturing sites in France and UK for medium and high current ion implantation services
- In addition IBS can perform MeV implants to 5 MeV and ULE implants as low as 1 keV.
- Whether it is for large volume manufacturing or single production runs, IBS has a solution to fit all customers needs.
- Independence, Quality (ISO 9001/2000) and Confidentiality

Your benefit



- Increase your capacity without heavy investments
- Efficient production back-up enables you to meet your delivery times
- Cost effective even for small volume
- Precise controls of contamination, uniformity and reproducibility
- Assistance in defining processes and/or choosing equipment



Standard implantation parameters

- Species: As, B, BF₂, P, Sb, Ar, N, Ge, Si, In, Ga, Al, ...
- Energy: from 2 to 250 keV
from 250 to 750 keV for double or triple charged ions
- Dose: from 1^{E10} at/cm² to 1^{E17} at/cm²
uniformity on 200mm wafers: <1%
wafer to wafer reproducibility: <1%
- Dimensions: wafers from 2" to 8"
- Tilt: from 0° to 10° in standard
from 0° to 160° upon request
- Rotation: available
- Cooling: available

Complementary steps :

- Photoresist pre-bake
- Resist stripping using plasma asher



Facilities :

- Ion implanters: NV8250P, NV6200, NV6200A, NV10-160, E500, 9500, CF3000/IMC, Pulsion
- Ultra fast service possible: 24h upon request
- Class 10 and 1 clean rooms
- Equipment with special handling for thin wafers

